低开关损耗、低导通电阻，有助于进一步节能

Low Switching Loss and ON Resistance Contribute to Greater Energy Savings

沟槽式 SiC MOSFET

Trench SiC MOSFET

SCT3 Series

特点

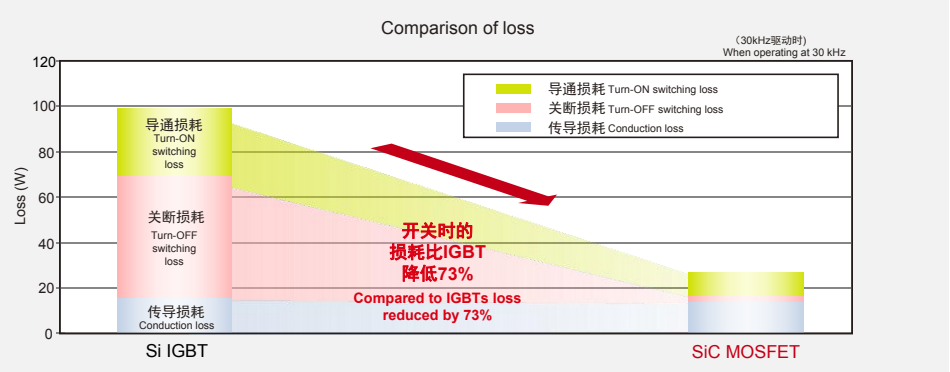
- **高速开关**
  High-speed switching
- **低导通电阻**
  Low ON-resistance
- **寄生二极管的反向恢复工作特性更佳**
  Minimal reverse recovery of body diode
- **功率损耗大幅降低，开关损耗降低73%**
  Significantly reduced switching loss by 73%

应用

- **太阳能功率调节器**
  PV power conditioner
- **电源**
  Power supply
- **车载(EV/PHEV)用充电器**
  Onboard charger for EV/PHEV
- **车载(EV/PHEV)用DC/DC转换器**
  DC/DC converter for EV/PHEV

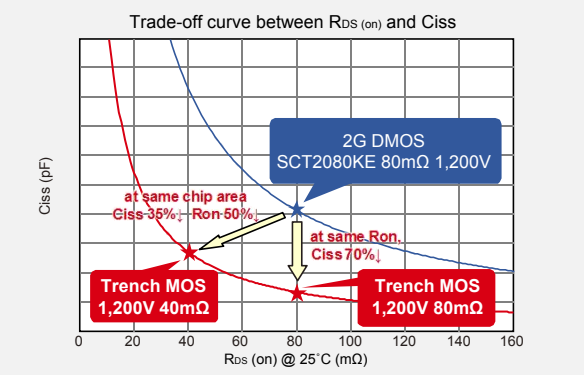
开关时的损耗大幅降低

Significantly Reduced Switching Loss



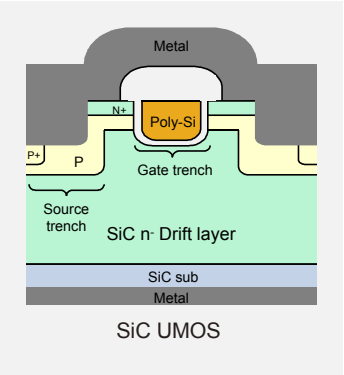
实现更低导通电阻

Further ON-Resistance reduction



结构图

Structural Diagram



产品阵容

Lineup

Generation	Part No.	Polarity (ch)	V_{DSS} (V)	I_D (A)	P_D (W) (T_C=25°C)	R_{DS}(on) Typ.(mΩ)	Qg Typ.(nC)		Automotive (AEC-Q101)	Package
						V_{GS}=18V	V_{GS}=18V	Drive Voltage (V)		
3rd	SCT3017AL	N	650	118	427	17	172	18	-	TO-247N
	SCT3022AL	N	650	93	339	22	133	18	-	
	SCT3030AL	N	650	70	262	30	104	18	-	
	SCT3060AL	N	650	39	165	60	58	18	-	
	SCT3080AL	N	650	30	134	80	48	18	-	
	SCT3120AL	N	650	21	103	120	38	18	-	
	SCT3022KL	N	1,200	95	427	22	178	18	-	
	SCT3030KL	N	1,200	72	339	30	131	18	-	
	SCT3040KL	N	1,200	55	262	40	107	18	-	
	SCT3080KL	N	1,200	31	165	80	60	18	-	
	New SCT3105KL	N	1,200	24	134	105	51	18	-	
	SCT3160KL	N	1,200	17	103	160	42	18	-	

Note : Package is JEDEC code. *Please contact us for automotive grade lineup.